



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92MOD Plastic-Encapsulate Transistors

2SA1283 TRANSISTOR (PNP)

FEATURE

Power dissipation

$$P_{CM} : 0.9 \text{ W (Tamb=25}^{\circ}\text{C)}$$

Collector current

$$I_{CM} : -1 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -60 \text{ V}$$

Operating and storage junction temperature range

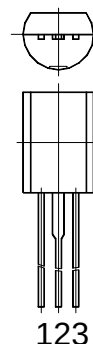
$$T_J, T_{stg} : -55^{\circ}\text{C to } +150^{\circ}\text{C}$$

TO-92MOD

1. EMITTER

2. COLLECTOR

3. BASE



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}$, $I_E = 0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -2\text{mA}$, $I_B = 0$	-60		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}$, $I_C = 0$	-6		V
Collector cut-off current	I_{CBO}	$V_{CB} = -50\text{ V}$, $I_E = 0$		-0.2	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{ V}$, $I_C = 0$		-0.2	μA
DC current gain	h_{FE}	$V_{CE} = -4\text{ V}$, $I_C = -100\text{mA}$	55	300	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -500\text{ mA}$, $I_B = -25\text{ mA}$		-0.3	V
Transition frequency	f_T	$V_{CE} = -2\text{V}$, $I_C = -10\text{mA}$	50		MHz
Output capacitance	C_{ob}	$V_{CE} = -10\text{V}$, $I_E = 0$, $f = 1\text{ MHz}$		25	pF

CLASSIFICATION OF h_{FE}

Rank	C	D	E
Range	55-110	90-180	150-300